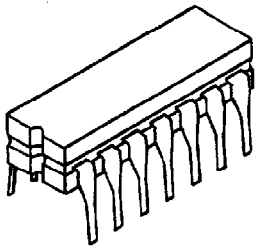


BRITISH STANDARDS INSTITUTION 2 PARK STREET, LONDON. W1A 2BS Specification available from:- AS SHOWN IN PD 9002 AND CECC 00 200 AND	BS CECC 90 104 - 183 ISSUE 1 DECEMBER 1981 Page 1 of 23 pages 
ELECTRONIC COMPONENTS OF ASSESSED QUALITY DETAIL SPECIFICATION IN ACCORDANCE WITH: BS CECC 90 000 : 1976 BS CECC 90 100 : 1977	MANUFACTURERS TYPE NUMBER 4562B SEE PD 9002 AND CECC 00 200 For ordering information see page 9
Outline not to scale: Isometric projection Marking information see page 8  For detail dimensions see IEC 191-2 (A50B)	128 BIT STATIC SHIFT REGISTER SILICON COMPLEMENTARY MOS. WITH (B) BUFFERED OUTPUTS AND CAVITY PACKAGING. Assessment levels R, S, T and V and optional screening categories A, B, C and D

CAUTION: THESE ARE STATIC SENSITIVE DEVICES - See clause 1.11

1. Limiting conditions of use (not for inspection purposes)

All voltages referenced to V_{SS}

1.1	Maximum supply voltage, positive	V_{DD}	+18,0V
1.2	Maximum supply voltage, negative	V_{DD}	-0,5V
1.3	Maximum positive input voltage	V_I	$V_{DD} + 0,5V$
1.4	Maximum negative input voltage	V_I	-0,5V

Refer to Qualified Products List PD 9002 and/or CECC 00 200
for details of manufacturers approved to this specification

1. Limiting conditions of use (contd)

1.5	Maximum power dissipation, per package	P_{D1}	200,0mW
	per output	P_{D2}	25,0mW
1.6	Maximum continuous current into any input.	$ I_I $	10,0mA
1.7	Maximum continuous current into any output.	$ I_O $	10,0mA
1.8	Operating temperature range	T_{amb}	
		Full	-55 to +125°C
		Limited	-40 to + 85°C
1.9	Storage temperature range	T_{stg}	-65 to +150°C
1.10	Transient energy rating		400V at 100pF through 1,5kΩ

1.11 Recommended handling precautions

- 1.11.1 Store devices in either conductive foam or conductive rails, or connect all leads together using a similar electrical shorting method.
- 1.11.2 Use grounded tip soldering irons.
- 1.11.3 Ground all test equipment.
- 1.11.4 Connect all unused device inputs to V_{DD} or V_{SS} .
- 1.11.5 PC boards used to mount MOS devices should have all metal leads grounded during device mounting or flow soldering operations.
- 1.11.6 Soldering equipment, solder pots or flow soldering equipment should be grounded whenever in contact with PC boards and/or MOS devices.
- 1.11.7 Do not use ungrounded automatic insertion equipment or other handling equipment that precludes the use of suitable device lead grounding techniques during inspection or handling.
- 1.11.8 When PC boards containing mounted MOS devices are removed from equipment for test, shipping or storage, 'Dummy connectors' should be used to electrically short all PC board terminals together.
- 1.11.9 Switch off power supply before inserting or removing devices from circuits.
- 1.11.10 Disconnect all low impedance equipment and input signals from the device before d.c. power supplies are switched off.

2. Recommended conditions of use and associated characteristics (not for inspection purposes)

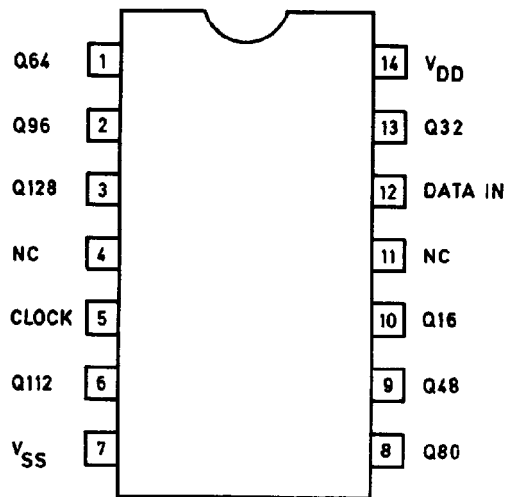
These apply over the operating temperature range unless otherwise stated. All voltages referenced to V_{SS} .

Characteristics	Conditions	Symbol	$V_{DD}(V)$	T_{amb} LOW	T_{amb} = 25°C	T_{amb} HIGH	Unit
Quiescent device current	$V_{IL} = 0V$ $V_{IH} = V_{DD}$						
Full temperature range	Outputs open circuit	I_{DDA}	5,0	5,0	5,0	150,0	μA
		I_{DDA}	10,0	10,0	10,0	300,0	μA
		I_{DDA}	15,0	20,0	20,0	600,0	μA
Limited temperature range		I_{DDA}	5,0	20,0	20,0	150,0	μA
		I_{DDA}	10,0	40,0	40,0	300,0	μA
		I_{DDA}	15,0	80,0	80,0	600,0	μA
LOW level output voltage at $ I_O < 1,0\mu A$	$V_{IL} = 0V$ $V_{IH} = V_{DD}$	V_{OLA}	5,0	0,05	0,05	0,05	V
		V_{OLA}	10,0	0,05	0,05	0,05	V
		V_{OLA}	15,0	0,05	0,05	0,05	V
HIGH level output voltage at $ I_O < 1,0\mu A$	$V_{IL} = 0V$ $V_{IH} = V_{DD}$	V_{OHB}	5,0	4,95	4,95	4,95	V
		V_{OHB}	10,0	9,95	9,95	9,95	V
		V_{OHB}	15,0	14,95	14,95	14,95	V
LOW level output voltage (for worst case combinations) at $ I_O < 1,0\mu A$	$V_{IL} = 1,5V$ $V_{IL} = 3,0V$ $V_{IL} = 4,0V$	V_{OLA}	5,0	0,5	0,5	0,5	V
		V_{OLA}	10,0	1,0	1,0	1,0	V
		V_{OLA}	15,0	1,5	1,5	1,5	V
HIGH level output voltage (for worst case combinations) at $ I_O < 1,0\mu A$	$V_{IH} = 3,5V$ $V_{IH} = 7,0V$ $V_{IH} = 11,0V$	V_{OHB}	5,0	4,5	4,5	4,5	V
		V_{OHB}	10,0	9,0	9,0	9,0	V
		V_{OHB}	15,0	13,5	13,5	13,5	V
Output LOW (sink) current							
Full temperature range	$V_O = 0,4V$	I_{OLB}	5,0	0,64	0,51	0,36	mA
	$V_O = 0,5V$	I_{OLB}	10,0	1,60	1,30	0,90	mA
	$V_O = 1,5V$	I_{OLB}	15,0	4,20	3,40	2,40	mA
Limited temperature range	$V_O = 0,4V$	I_{OLB}	5,0	0,52	0,44	0,36	mA
	$V_O = 0,5V$	I_{OLB}	10,0	1,30	1,10	0,90	mA
	$V_O = 1,5V$	I_{OLB}	15,0	3,60	3,00	2,40	mA

Characteristics	Conditions	Symbol	$V_{DD}(V)$	T_{amb} LOW	T_{amb} = 25°C	T_{amb} HIGH	Unit
Output HIGH (source) current							
Full temperature range	$V_O = 4,6V$	$-I_{OHB}$	5,0	0,64	0,51	0,36	mA
	$V_O = 9,5V$	$-I_{OHB}$	10,0	1,60	1,30	0,90	mA
	$V_O = 13,5V$	$-I_{OHB}$	15,0	4,20	3,40	2,40	mA
Limited temperature range	$V_O = 4,6V$	$-I_{OHB}$	5,0	0,52	0,44	0,36	mA
	$V_O = 9,5V$	$-I_{OHB}$	10,0	1,30	1,10	0,90	mA
	$V_O = 13,5V$	$-I_{OHB}$	15,0	3,60	3,00	2,40	mA
Input leakage current	$V_{IL} = 0V$ $V_{IH} = V_{DD}$						
Full temperature range		$ I_{IA} $	15,0	0,10	0,10	1,00	μA
Limited temperature range		$ I_{IA} $	15,0	0,30	0,30	1,00	μA
Input capacitance per unit load (Any input)	$V_I = 0V$ $f = 1MHz$	C_{IA}	-	-	7,5	-	pF
Noise margin at LOW level output (equal to the difference between V_{IL} and V_{OL} for worst case combinations)		V_{NLB}	5,0	1,0	1,0	1,0	V
		V_{NLB}	10,0	2,0	2,0	2,0	V
		V_{NLB}	15,0	2,5	2,5	2,5	V
Noise margin at HIGH level output (equal to the difference between V_{IH} and V_{OH} for worst case combinations)		V_{NHB}	5,0	1,0	1,0	1,0	V
		V_{NHB}	10,0	2,0	2,0	2,0	V
		V_{NHB}	15,0	2,5	2,5	2,5	V
Propagation and Transition Times	$C_L = 50pF$ (Test conditions as in Sub-group A5)						

Characteristics	Conditions	Symbol	V _{DD} (V)	T _{amb} LOW	T _{amb} = 25°C	T _{amb} HIGH	Unit
Propagation Delay Time HIGH to LOW and LOW to HIGH level Clock to Q		t _{PLHA} /	5,0	-	1200,0	-	ns
		t _{PHLA}	10,0	-	500,0	-	ns
			15,0	-	340,0	-	ns
Transition Time LOW to HIGH level Transition Time HIGH to LOW level		t _{TLHA}	5,0	-	360,0	-	ns
		t _{TLHA}	10,0	-	180,0	-	ns
		t _{TLHA}	15,0	-	130,0	-	ns
		t _{THLA}	5,0	-	200,0	-	ns
		t _{THLA}	10,0	-	100,0	-	ns
		t _{THLA}	15,0	-	80,0	-	ns
Clock Pulse Width (50% duty cycle)		t _{PWCB}	5,0	-	600,0	-	ns
		t _{PWCB}	10,0	-	220,0	-	ns
		t _{PWCB}	15,0	-	150,0	-	ns
Clock Pulse Frequency		Freq.A	5,0	-	1,1	-	MHz
		Freq.A	10,0	-	3,0	-	MHz
		Freq.A	15,0	-	4,0	-	MHz
Data to Clock Set-up Time		t _{PWST}	5,0	-	-20,0	-	ns
		(L)B/	10,0	-	-10,0	-	ns
		t _{PWST} (H)B	15,0	-	0,0	-	ns
Data to Clock Hold Time (LOW) Data to Clock Hold Time (HIGH)		t _{PWH(L)B}	5,0	-	350,0	-	ns
		t _{PWH(L)B}	10,0	-	200,0	-	ns
		t _{PWH(L)B}	15,0	-	140,0	-	ns
		t _{PWH(H)B}	5,0	-	350,0	-	ns
		t _{PWH(H)B}	10,0	-	165,0	-	ns
		t _{PWH(H)B}	15,0	-	155,0	-	ns

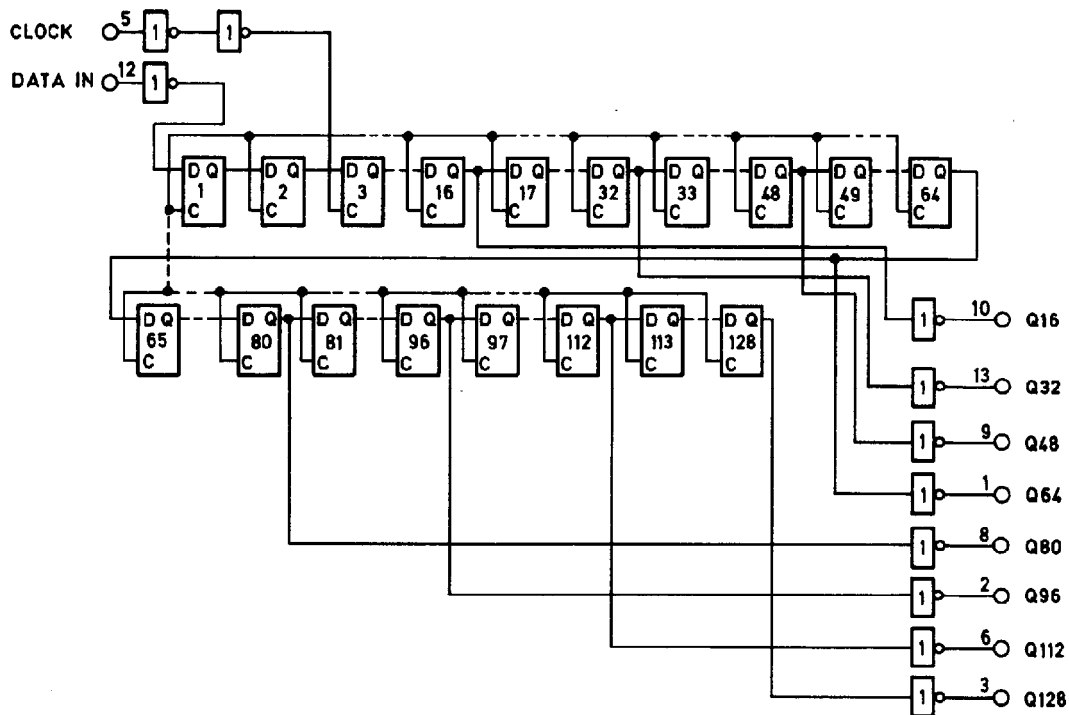
Terminal identification



Terminals marked with NC are not connected internally and may be used as electrical support points.

Figure 1

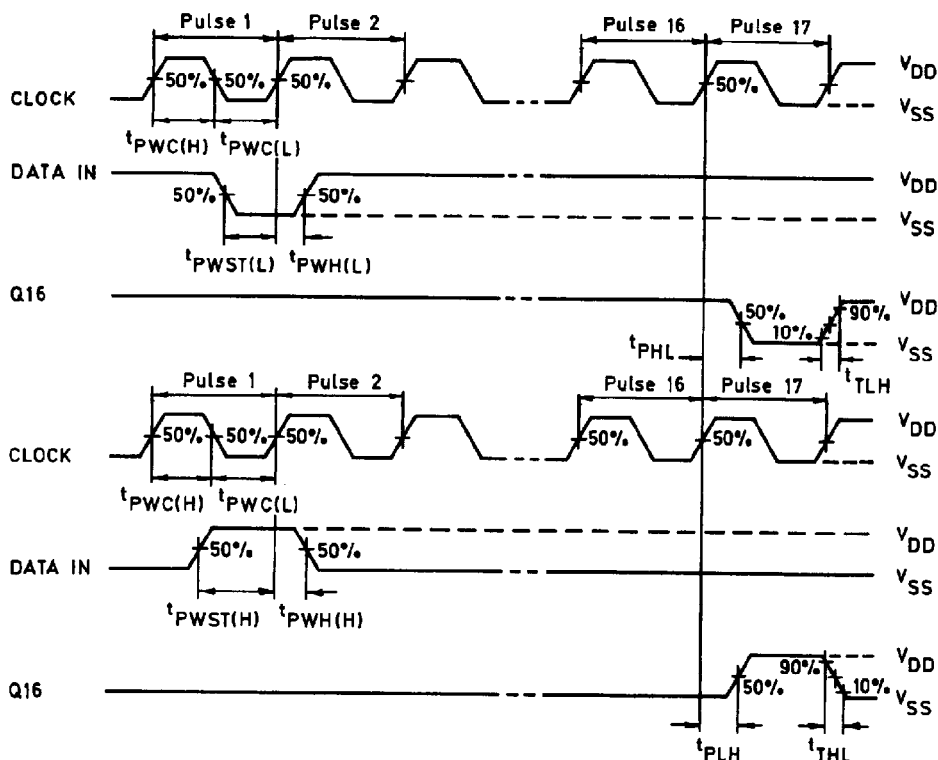
Typical logic diagram



This is a graphic representation, not a circuit diagram

Figure 2

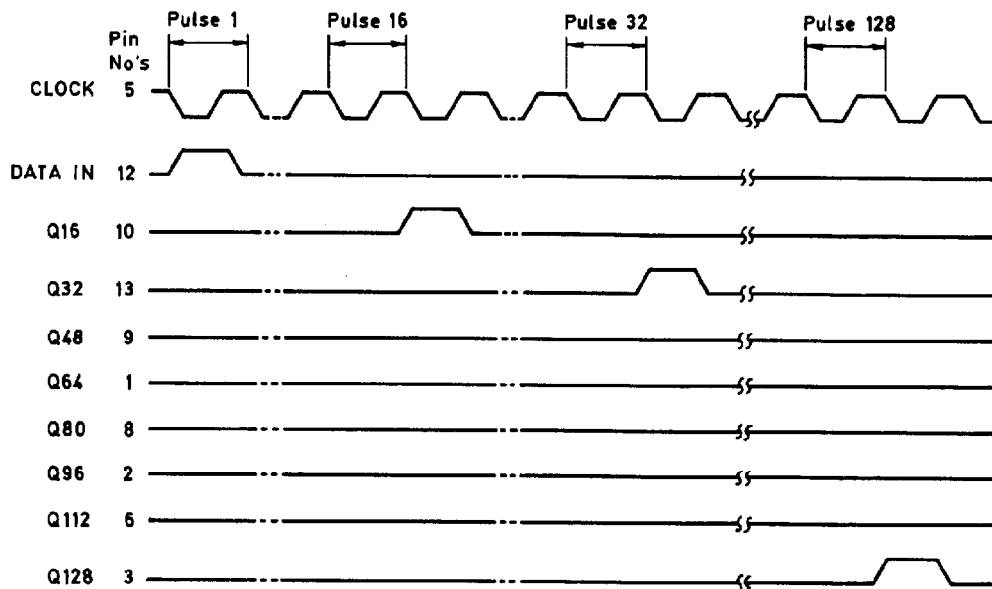
Switching time waveforms



NOTE The remaining Data - Bit Outputs (Q32, Q48, Q64, Q80, Q96, Q112 and Q128) will occur at Clock Pulse 32, 48, 64, 80, 96, 112, 128 in the same relationship as Q16.

Figure 3

Timing diagram



NOTE Q48 to Q96 will occur in the same relationship with Clock Pulses 48 to 96 as do Q16 and Q32 with Clock Pulse 16 and 32.

Figure 4